



Docket No.: M4065.0609/P609-C
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Jiutao Li

Application No.: 10/758,008

Confirmation No.: 6244

Filed: January 16, 2004

Art Unit: 2815

For: AGGLOMERATION ELIMINATION FOR
METAL SPUTTER DEPOSITION OF
CHALCOGENIDES

Examiner: J. A. Fenty

**REQUEST FOR
ACKNOWLEDGEMENT OF FORM PTO-1449**

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In reviewing the above-captioned application file, the undersigned has noticed that the Applicant's Form PTO-1449, which accompanied an Information Disclosure Statement submitted on January 16, 2004, has not been acknowledged by the Examiner. A copy of the initialed Form PTO-1449 was not included with the Final Office Action dated March 10, 2005. The Examiner is therefore kindly requested to return the initialed forms to the undersigned as soon as possible.

Application No.: 10/758,008

Docket No.: M4065.0609/P609-C

Dated: May 23, 2005

Respectfully submitted,

By



Thomas J. D'Amico

Registration No.: 28,371

Elizabeth Parsons

Registration No.: 52,499

DICKSTEIN SHAPIRO MORIN &
OSHINSKY LLP

2101 L Street NW

Washington, DC 20037-1526

(202) 785-9700

Attorneys for Applicant



Docket No.: M4065.0609/P609-C
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Jiutao Li

Application No.: NEW

Confirmation No.:

Filed: January 16, 2003

Art Unit: N/A

For: AGGLOMERATION ELIMINATION
FOR METAL SPUTTER DEPOSITION
OF CHALCOGENIDES

Examiner: Not Yet Assigned

INFORMATION DISCLOSURE STATEMENT (IDS)

MS Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Pursuant to 37 CFR 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO/SB/08. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement accompanies the new patent application submitted herewith.

Those patent(s) or publication(s) which are marked with an asterisk (*) in the attached form PTO/SB/08 are not supplied because they were previously cited by or submitted to the Office in a prior application no. 09/809,331, filed March 15, 2001, and relied upon in this application for an earlier filing date under 35 U.S.C. 120.

In accordance with 37 CFR 1.97(g), the filing of this Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information as defined in 37 CFR 1.56(a) exists. In accordance with 37 CFR 1.97(h), the filing of this Information Disclosure statement shall not be construed to be an admission that any patent, publication or other information referred to therein is "prior art" for this invention unless specifically designated as such.

It is submitted that the Information Disclosure Statement is in compliance with 37 CFR 1.98 and the Examiner is respectfully requested to consider the listed references.

The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.0609/P609-C. A duplicate copy of this paper is enclosed.

Dated: January 16, 2004

Respectfully submitted,

By 

Thomas J. D'Amico

Registration No.: 28,371

DICKSTEIN SHAPIRO MORIN &

OSHINSKY LLP

2101 L Street NW

Washington, DC 20037-1526

(202) 785-9700

Attorney for Applicant



PTO/SB/08A (10-01)
Approved for use through 10/31/2002. OMB 0651-0031
U. S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO <h2 style="margin: 0;">INFORMATION DISCLOSURE STATEMENT BY APPLICANT</h2> <p style="margin: 5px 0 0 40px;">(use as many sheets as necessary)</p>				Complete If Known	
Application Number				NEW	
Filing Date				January 7, 2004	
First Named Inventor				Jiutao Li	
Art Unit				N/A	
Examiner Name				Not Yet Assigned	
Attorney Docket Number				M4065.0609/P609/P609-C	

Sheet	1	of	9
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U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (# known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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				Art Unit	N/A
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Sheet	2	of	9	Attorney Docket Number	M4065.0609/P609/P609-C

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FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Country Code ²	Number ³ -Kind Code ⁴ (if known)			
	BA	WO	02/21542*	03/14/2002	Kozicki et al.	
	BB	WO	00/48196*	08/17/2000	Kozicki et al.	
	BC	WO	97/48032*	12/18/1997	Kozicki et al.	
	BD	WO	99/28914*	06/10/1999	Kozicki et al.	
	BE	JP	56126916*	10/1981	Akira et al.	

Examiner Signature		Date Considered	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete If Known	
				Application Number	NEW
				Filing Date	January 7, 2004
				First Named Inventor	Jiutao Li
				Group Art Unit	N/A
				Examiner Name	Not Yet Assigned
Sheet	3	of	9	Attorney Docket Number	M4065.0609/P609/P609-C

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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	CG	Aleksiejunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19 (1973) K169-K171.	
	CH	Angell, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717.	
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	CQ	Bernede, J.C., Polarized memory switching in MIS thin films, Thin Solid Films 81 (1981) 155-160.	
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Sheet	4	of	9	Attorney Docket Number	M4065.0609/P609/P609-C

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